



U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. IMEC278.001AUS	APPLICATION NO. 10/603,428
	APPLICANT Van Houdt, et al.	
	FILING DATE June 24, 2003	GROUP 2818

SHEET 1 OF 2

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
<i>Ah</i>	1	4,794,565	12/27/88	Wu, et al.			
	2	5,278,439	01/11/94	Ma, et al.			
	3	5,280,446	01/18/94	Ma, et al.			
	4	5,284,784	02/08/94	Manley			
	5	5,338,952	08/16/94	Yamauchi			
	6	5,394,360	02/28/95	Fukumoto			
	7	5,538,811	12/10/96	Van Houdt, et al.			
	8	5,841,697	11/24/98	Van Houdt, et al.			
	9	6,044,015	03/28/00	Van Houdt, et al.			
	10	6,366,500 B1	04/02/02	Ogura, et al.			
	11	6,580,120 B1	06/17/03	Haspeslagh			
<i>Ah</i>	12	2002/0005545 A1	01/17/02	Widdershoven, et al.			

FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO
<i>Ah</i>	13	EP 1 096 572 A1	05/02/01	EUROPE			

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
<i>Ah</i>	14	Esquivel, et al., "High density contactless, self aligned EPROM cell array technology", IEDM Tech. Dig., pp. 592-595, (1986).
	15	Hayashi, et al., "Twin MONOS cell with dual control gates", IEEE, presented at the 2000 Symposium on VLSI Technology Digest of Technical Papers, pp. 122-123, (2000).
	16	<i>Microlithography, Science and Technology</i> , Sheets, et al., Eds., Marcel Dekker, Inc., New York, New York, pp. 515-565 and 615-644, (1998).
	17	Miyawaki, et al., "A new erasing and row decoding scheme for low supply voltage operation 16-Mb/64-Mb flash memories", IEEE Journal of Solid-State Circuits, vol. 27, no. 4, pp. 583-588, (April 1992).
	18	Tanaka, et al., "A quick intelligent page-programming architecture and a shielded bitline sensing method for 3V-only NAND flash memory", IEEE Journal of Solid-State Circuits, vol. 29, no. 11, pp. 1366-1373, (November 1994).
<i>Ah</i>	19	Van Houdt, et al., "A 5-volt-only fast-programming flash EEPROM cell with a double polysilicon split-gate structure", presented at the 11 th IEEE Non-volatile Semiconductor Memory Workshop, (February 1991).

EXAMINER	<i>Andrea Huyer</i>	DATE CONSIDERED	<i>07/19/04</i>
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED. INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.			



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EXAMINER INITIAL		OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
Ah	20	Van Houdt, et al., "Analysis of the enhanced hot-electron injection in split-gate transistors useful for EEPROM applications", IEEE Transactions on Electron Devices, vol. 39, no. 5, pp. 1150-1156, (May 1992).	
I	21	Van Houdt, et al., "HIMOS-A high efficiency flash E2PROM cell for embedded memory applications", IEEE Transactions on Electron Devices, vol. 40, no. 12, pp. 2255-2263, (December 1993).	
Ah	22	Yamauchi, et al., "A 5V-only virtual ground flash cell with an auxillary gate for high density and high speed application", IEDM Tech. Dig., p. 319-322, (1991).	

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